AMENDMENTS TO THE CLAIMS

The listing of claims below replaces all prior versions of claims in the application.

Claim 1 (Previously presented): An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, provided with a T-shaped gate electrode comprised of a trunk-shaped main gate electrode extending in parallel with respect to said semiconductor substrate, and a crosspiece-shaped conductor pattern extending in parallel with respect to said semiconductor substrate and also extending toward the width direction of said main gate electrode and having a length larger than the width of source and drain regions, and having a thickness of a gate insulating film formed directly under the entire region of the crosspiece-shaped conductor pattern greater than the thickness of the gate insulating film directly under the main gate electrode.

Claim 2 (Previously Presented): An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, wherein a thickness of a first insulating film provided on a surface of a first conductivity type semiconductor region positioned at an interface between a first conductivity type body contact region, for draining carriers stored at a channel region under a gate electrode, and a second conductivity type source and drain regions is made greater than the thickness of a second insulating film, acting as a gate insulating film, with a uniform thickness directly under said gate electrode, said gate electrode being provided on the region

except for said body contact region, said first insulating film abutting against the one end of said gate electrode and extending in a direction perpendicular to said gate electrode along said interface.

Claim 3 (Previously presented): An insulated gate type semiconductor device as set forth in claim 2, said first insulating film is formed as a buried insulating film.

Claim 4 (Cancelled).

Claim 5 (Previously presented): An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, said active region including a first conductivity type body contact region and second conductivity type source and drain regions, said body contact region contacting with said source region, wherein a gate electrode of a shape of asymmetric T-shape comprised of a trunk-shaped main gate electrode extending in parallel with respect to said semiconductor substrate, and a crosspiece-shaped conductor pattern extending in parallel with respect to said semiconductor substrate and also extending toward the width direction of said main gate electrode is provided above said active region and, said trunk-shaped main gate electrode is sandwiched between said source region formed without contacting with said crosspiece-shaped conductor pattern and said drain region, and at least part of said crosspiece-shaped conductor pattern is also sandwiched between said source region formed between said

crosspiece-shaped conductor pattern and said body contact region and said drain region, and thereby at least part of said crosspiece-shaped conductor pattern functions as an effective gate electrode.

Claim 6 (Withdrawn): A method for fabricating an insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, comprising the steps of:

providing a gate insulating film partially differing in thickness on the surface of said semiconductor layer;

providing a crosspiece-shaped conductor pattern on a thick portion of said gate insulating film and providing a trunk-shaped main gate electrode on the gate insulating film to form a T-shaped gate electrode;

forming sidewalls on side faces of said gate electrode;

doping an impurity using said main gate electrode and crosspiece-shaped conductor pattern as a mask to form source and drain regions;

doping an impurity using said crosspiece-shaped conductor pattern as a mask to form a body contact region; and

depositing a metal film over the entire surface and then performing heat treatment to form a silicide electrode.

Claim 7 (Withdrawn): A method for fabricating an insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, comprising the steps of:

providing a gate insulating film partially differing in thickness on the surface of said semiconductor layer;

providing a crosspiece-shaped conductor pattern on a thick portion of said gate insulating film and providing a trunk-shaped main gate electrode on the gate insulating film to form a T-shaped gate electrode;

forming sidewalls on side faces of said gate electrode;

doping an impurity using said main gate electrode and crosspiece-shaped conductor pattern as a mask to form source and drain regions;

doping an impurity using said crosspiece-shaped conductor pattern as a mask to form a body contact region; and

removing said crosspiece-shaped conductor pattern, then depositing a metal film over the entire surface and performing heat treatment to form a silicide electrode.

Claim 8 (Withdrawn): A method for fabricating an insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, comprising the steps of:

forming a groove of a different depth in the surface of said semiconductor layer and burying the groove by an insulator to form an element isolation insulating film and an intra-element isolation insulating film;

providing a gate electrode on a gate insulating film;

forming sidewalls on side faces of said gate electrode;

doping an impurity using said gate electrode and said intra-element isolation insulating film as a mask to form source and drain regions;

doping an impurity using said intra-element isolation insulating film as a mask to form a body contact region; and

depositing a metal film over the entire surface and then performing heat treatment to form a silicide electrode.

Claim 9 (Cancelled).